	Туре	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L4	1126	semiconductor adj substrate and (sims or secondary adj ion adj mass adj spectroscopy)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:19
2	BRS	L5	1529	semiconductor adj substrate and (sims or secondary adj ion adj mass adj spectroscopy)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:19
3	BRS	L6	67	doping adj profile and 5	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:19
4	BRS	L7	774	(planarize or planarizing or cmp or chemical adj mechanical adj polishing) and (sims or secondary adj ion adj mass adj spectroscopy)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:20
5	BRS	L8	4090	doping adj profile	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:20

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	Туре	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L9	17	7 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:20
7	BRS	L10	8	(planarize or planarizing) same doping adj profile	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:21
8	BRS	L11	26606	sims or secondary adj ion adj mass adj spectroscopy	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:21
9	BRS	L12	2		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:22
10	BRS	L13	6	(planarize or planarizing) same sims	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 13:23

	Туре	L #	Hits	Search Text	DBs	Time Stamp
11	IS&R	L19	1385	(438/14).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 14:42
12	IS&R	L25	420	(438/18).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 15:12
13	IS&R	<b>L26</b>	227	(250/370.14).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 15:16
14	IS&R	L27	1610	(250/306).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 15:28
15	IS&R	L28	338	(324/71.5).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 15:34

	Туре	L #	Hits	Search Text	DBs	Time Stamp
16	IS&R	L29	413		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/03/31 16:00

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